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15. (Amended) The method of claim 5, further comprising:
repeating said depositing a conducting material; and
repeating said depositing a metal over the conducting material, thereby depositing
subsequent said conducting material and said metal on the resulting structure.

Please add the following new claims:

18. The method of claim 16, wherein said conducting material comprises one of a
chemical vapor deposition metal, a physical vapor deposition metal, and a plated liner.

19. The method of claim 16, wherein said contacts comprise contacts formed between
first and second metal levels formed on the semiconductor substrate.

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20. The method of claim 16, wherein said selectively removing comprises selectively
removing said conductive material by a selective etch.

21. The method of claim 1, wherein said relatively narrow first structure is not connected
on said substrate to said relatively wider second structure.

22. The method of claim 1, wherein said forming a relatively wider second structure
forms said wider structure on said substrate apart from said relatively narrow structure.

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23. The method of claim 5, wherein said contact is not connected in said substrate to said
trough.

24. The method of claim 5, wherein said forming troughs forms said troughs in said
dielectric apart from said contact.

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